

REMARKS

This Supplemental Amendment is submitted herewith to correct a typographical error in claim 4. Specifically, line 9, "and" has been omitted and should read "semiconductor layer so that said second and third insulating films are in direct contact to each other."

Respectfully submitted,



Eric J. Robinson
Reg. No. 38,285

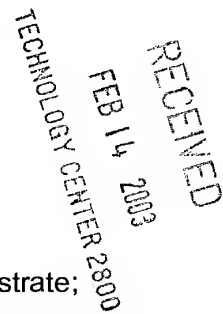
Robinson Intellectual Property Law Office, P.C.
PMB 955
21010 Southbank Street
Potomac Falls, Virginia 20165
(571) 434-6789

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VERSION WITH MARKINGS TO SHOW CHANGES MADE

IN THE CLAIMS:

Please amend claim 4 as follows:



4. (Amended) A semiconductor device comprising:
- a first insulating film comprising silicon nitride formed on a substrate;
 - a second insulating film comprising silicon oxide formed on said first insulating film;
 - a semiconductor layer formed on said second insulating film wherein said semiconductor layer includes at least source, drain and channel regions;
 - a third insulating film comprising silicon oxide formed on said semiconductor layer wherein said third insulating film extends beyond edges of said semiconductor layer so that said second and third insulating films are in direct contact to each other;
 - a fourth insulating film comprising silicon nitride formed on said third insulating film wherein said fourth insulating film covers said semiconductor layer extends beyond side edges of the semiconductor layer;
 - a gate electrode formed over said channel region with said third and fourth insulating films interposed therebetween.

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